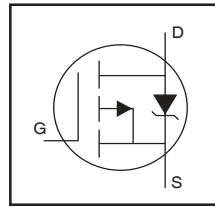


AUIRF9540N

Features

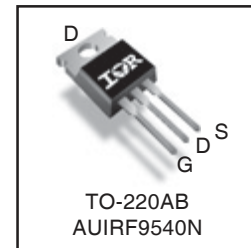
- Advanced Planar Technology
- Dynamic dV/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to T_{jmax}
- Lead-Free, RoHS Compliant
- Automotive Qualified*



V_{(BR)DSS}	-100V
R_{DS(on)} max.	0.117Ω
I_D	-23A

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	-23	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	-16	
I _{DM}	Pulsed Drain Current ①	-76	
P _D @ T _C = 25°C	Power Dissipation	140	W
	Linear Derating Factor	0.91	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy (Thermally Limited)②	430	mJ
I _{AR}	Avalanche Current ①	-11	A
E _{AR}	Repetitive Avalanche Energy ①	14	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)		
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ④	—	1.1	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface	0.50	—	
R _{θJA}	Junction-to-Ambient	—	62	

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*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.11	—	V/°C	Reference to 25°C, I _D = -1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.117	Ω	V _{GS} = -10V, I _D = -11A ④
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	5.3	—	—	S	V _{DS} = -50V, I _D = -11A
I _{DSS}	Drain-to-Source Leakage Current	—	—	-25	μA	V _{DS} = -100V, V _{GS} = 0V
		—	—	-250		V _{DS} = -80V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge	—	—	97	nC	I _D = -11A
Q _{gs}	Gate-to-Source Charge	—	—	15		V _{DS} = -80V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	51		V _{GS} = -10V, See Fig. 6 & 13 ④
t _{d(on)}	Turn-On Delay Time	—	15	—	ns	V _{DD} = -50V
t _r	Rise Time	—	67	—		I _D = -11A
t _{d(off)}	Turn-Off Delay Time	—	51	—		R _G = 5.1Ω
t _f	Fall Time	—	51	—		R _D = 4.2Ω, See Fig. 10 ④
L _D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	7.5	—		
C _{iss}	Input Capacitance	—	1300	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	400	—		V _{DS} = -25V
C _{rss}	Reverse Transfer Capacitance	—	240	—		f = 1.0MHz, See Fig. 5

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-23	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	-76		
V _{SD}	Diode Forward Voltage	—	—	-1.6	V	T _J = 25°C, I _S = -11A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	150	220	ns	T _J = 25°C, I _F = -11A
Q _{rr}	Reverse Recovery Charge	—	830	1200	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting T_J = 25°C, L = 7.1mH, R_G = 25Ω, I_{AS} = -11A. (See Figure 12)
- ③ I_{SD} ≤ -11A, di/dt ≤ -470A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ R_θ is measured at T_J approximately 90°C.

Qualification Information†

Qualification Level		Automotive (per AEC-Q101) ††	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		TO-220	N/A
ESD	Machine Model	Class M4 (+/- 500V) ††† AEC-Q101-002	
	Human Body Model	Class H1 (+/- 2000V) ††† AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) ††† AEC-Q101-005	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage

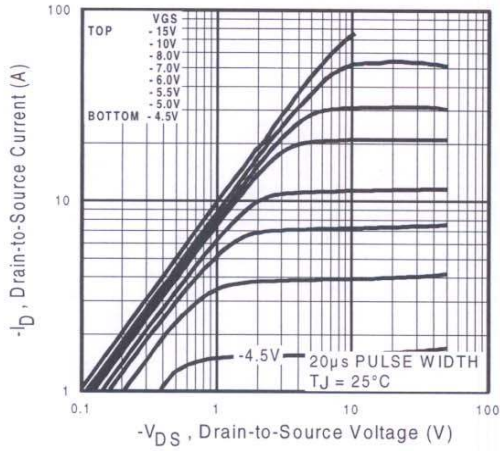


Fig 1. Typical Output Characteristics

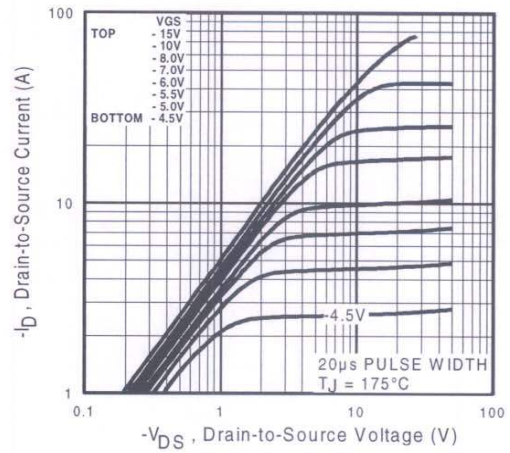


Fig 2. Typical Output Characteristics

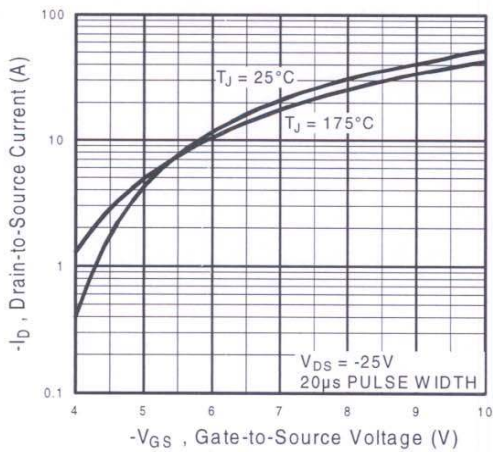


Fig 3. Typical Transfer Characteristics

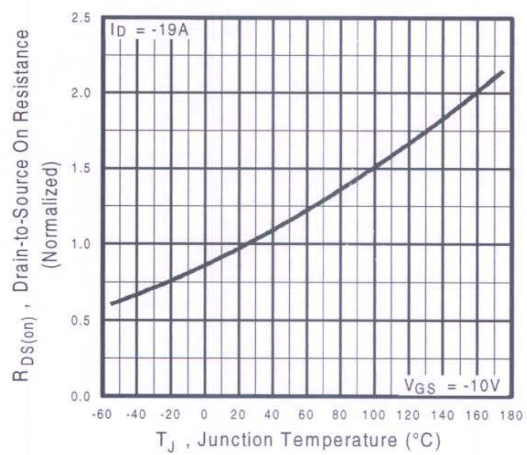


Fig 4. Normalized On-Resistance Vs. Temperature

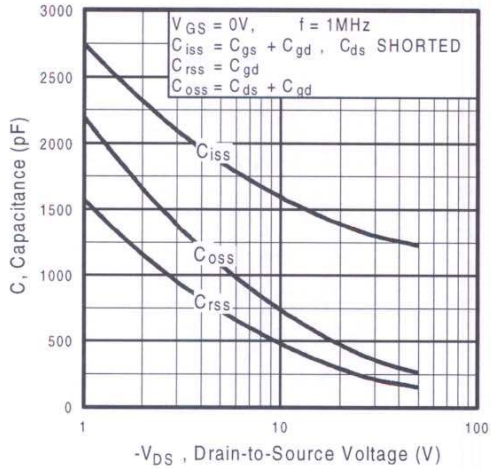


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

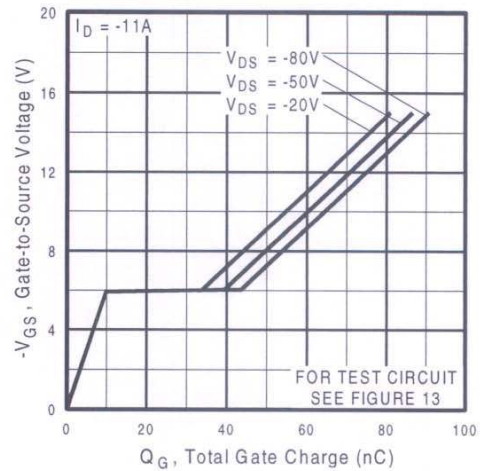


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

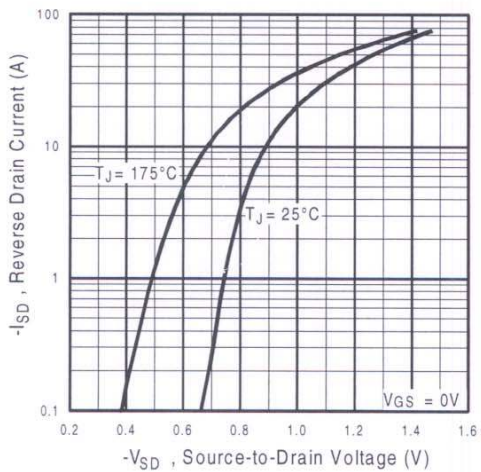


Fig 7. Typical Source-Drain Diode Forward Voltage

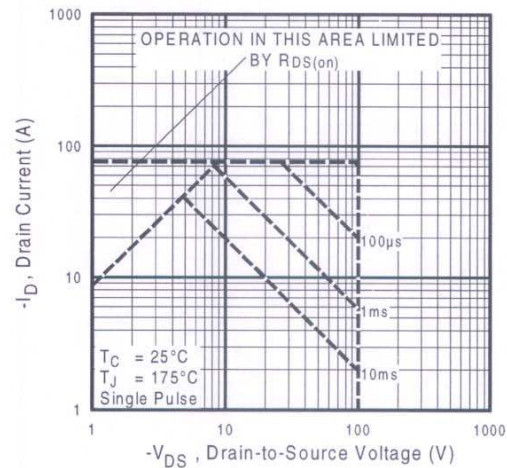


Fig 8. Maximum Safe Operating Area

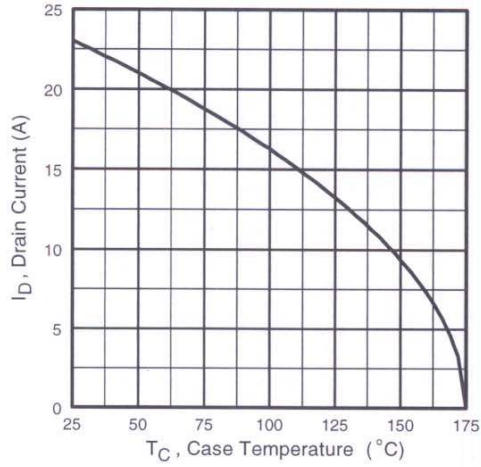


Fig 9. Maximum Drain Current Vs. Case Temperature

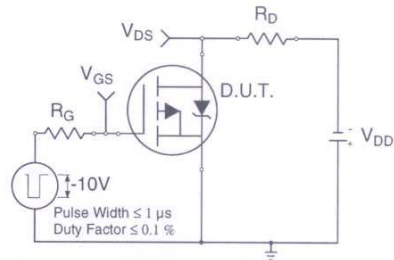


Fig 10a. Switching Time Test Circuit

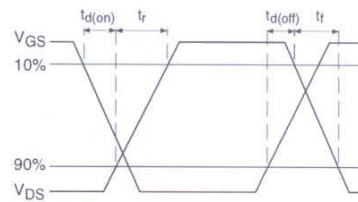


Fig 10b. Switching Time Waveforms

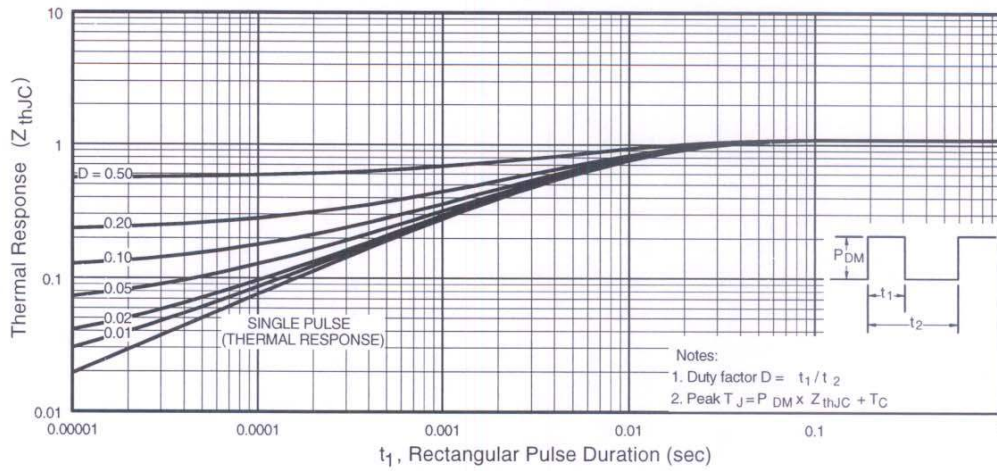


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

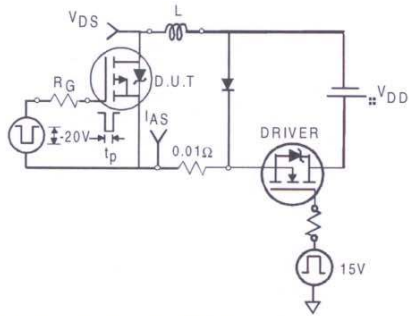


Fig 12a. Unclamped Inductive Test Circuit

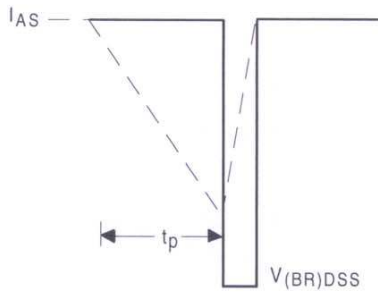


Fig 12b. Unclamped Inductive Waveforms

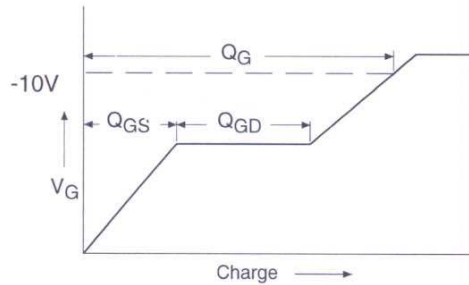


Fig 13a. Basic Gate Charge Waveform

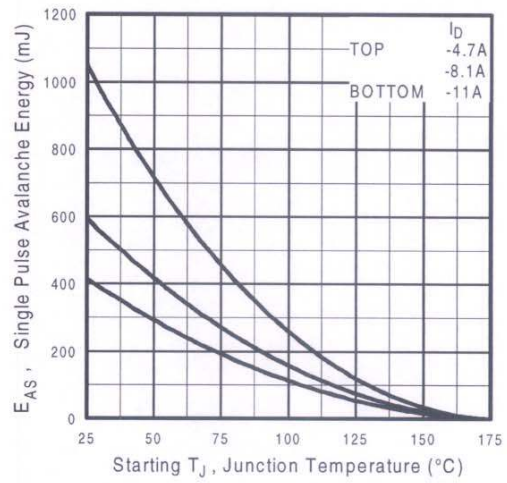


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

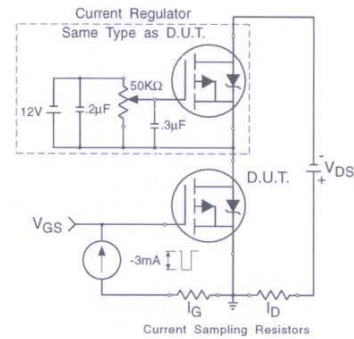


Fig 13b. Gate Charge Test Circuit

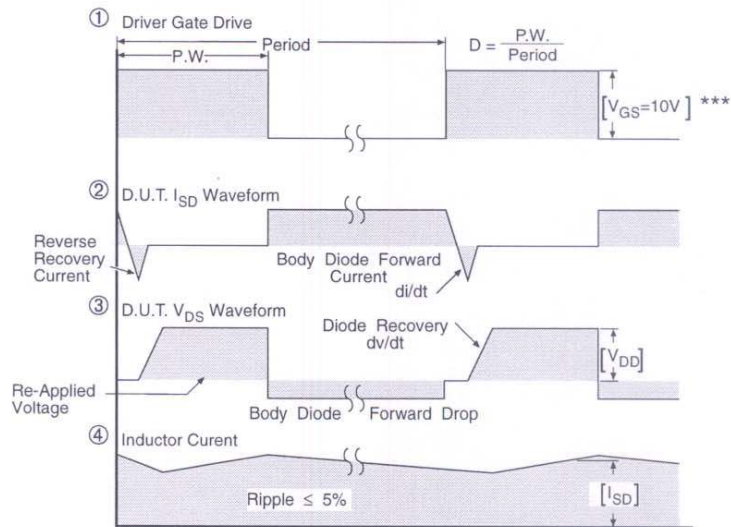
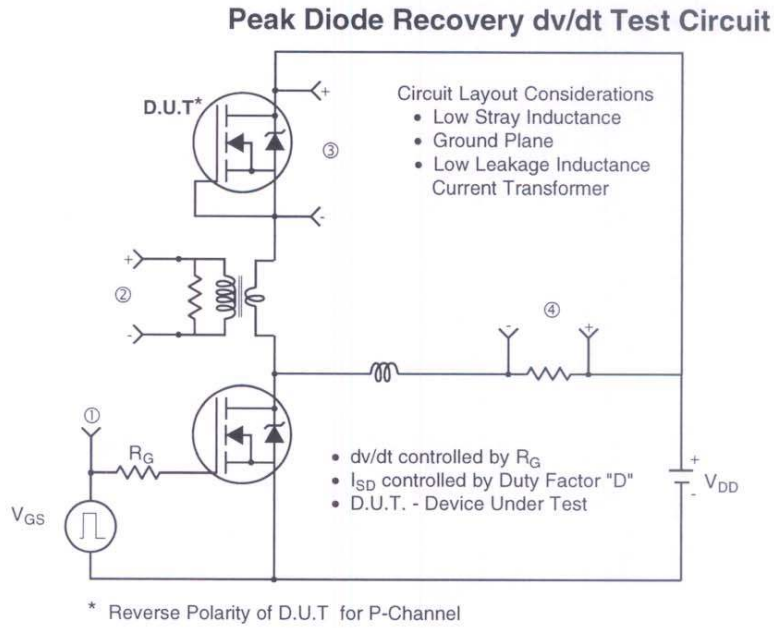
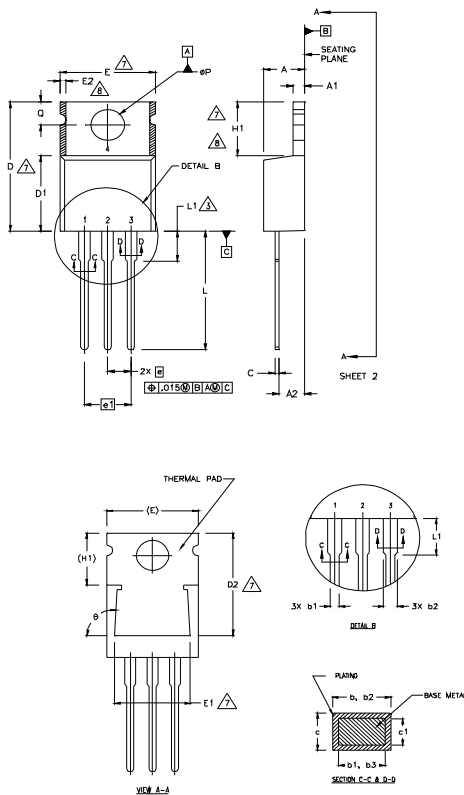


Fig 14. For P-Channel HEXFETS

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
- 6 CONTROLLING DIMENSION : INCHES.
- 7 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

LEAD ASSIGNMENTS

- HEFET
1.- GATE
2.- DRAIN
3.- SOURCE

IGBTs, CoPACK

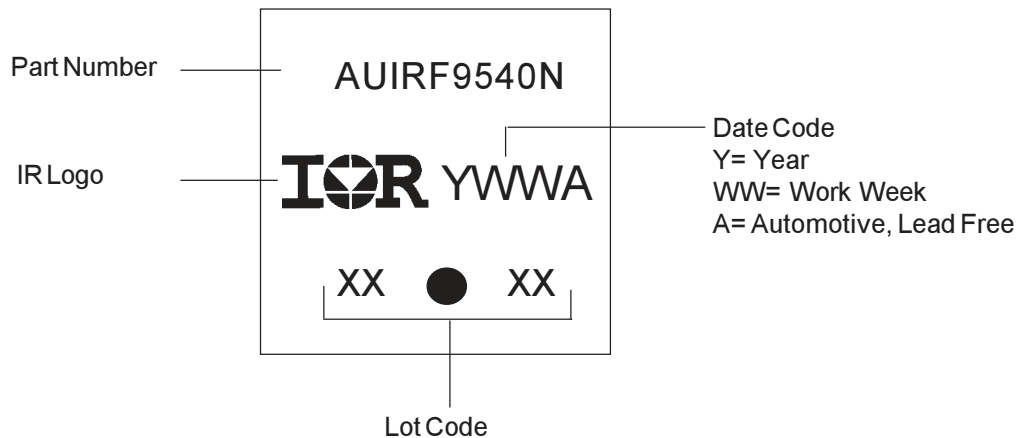
- 1.- GATE
2.- COLLECTOR
3.- EMITTER

DIODES

- 1.- ANODE/OPEN
2.- CATHODE
3.- ANODE

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.82	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.04	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.96	.015	.038	5
b2	1.15	1.77	.045	.070	
b3	1.15	1.73	.045	.068	
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	12.19	12.88	.480	.507	7
E	9.66	10.66	.380	.420	4,7
E1	8.38	8.89	.330	.350	7
e	2.54 BSC		.100 BSC		
e1	5.08		.200 BSC		
H1	5.85	6.55	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	-	6.35	-	.250	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	
ø	90°-93°		90°-93°		

TO-220AB Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>
www.irf.com

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF9540N	TO-220	Tube	50	AUIRF9540N

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WORLD HEADQUARTERS:
101 N. Sepulveda Blvd., El Segundo, California 90245
Tel: (310) 252-7105